TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7MH540FK, TC7MH541FK

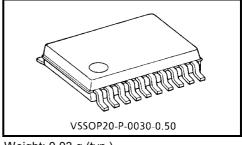
Octal Bus Buffer

TC7MH540FK Inverted, 3-State Outputs
TC7MH541FK Non-Inverted, 3-State Outputs

The TC7MH540FK and TC7MH541FK are advanced high speed CMOS octal bus buffers fabricated with silicon gate $\rm C^2MOS$ technology.

They achieve the high speed operation similar to equivalent bipolar schottky TTL while maintaining the CMOS low power dissipation.

The TC7MH540FK is an inverting type, and the TC7MH541FK is a non-inverting type.



Weight: 0.03 g (typ.)

When either $\overline{G}1$ or $\overline{G}2$ are high, the terminal outputs are in the high-impedance state.

An input protection circuit ensures that 0 to 7 V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5 V to 3 V systems and two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

Features

- High speed: $t_{pd} = 3.7 \text{ ns (typ.) (VCC} = 5 \text{ V)}$
- Low power dissipation: $ICC = 4 \mu A \text{ (max) (Ta} = 25 \text{°C)}$
- High noise immunity: V_{NIH} = V_{NIL} = 28% V_{CC} (min)
- Power down protection is provided on all inputs.
- Balanced propagation delays: t_pLH ≃ t_pHL
- Wide operating voltage range: VCC (opr) = 2~5.5 V
- Low noise: VOLP = 1.0 V (max)
- Pin and function compatible with 74ALS540/541

000630EBA

In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc..

The products described in this document are subject to the foreign exchange and foreign trade laws

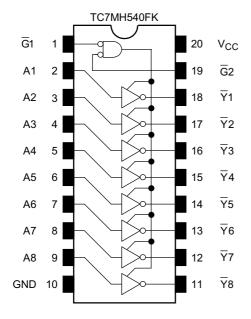
• The information contained herein is subject to change without notice.

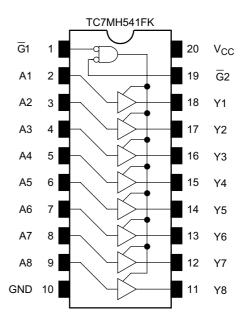
TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general
can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the
buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and
to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or
damage to property.

[•] The Toshiba products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These Toshiba products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of Toshiba products listed in this document shall be made at the customer's own risk.

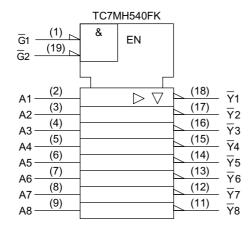
The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others

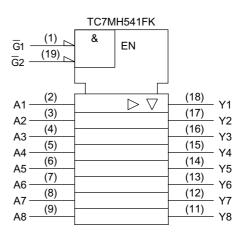
Pin Assignment (top view)





IEC Logic Symbol





Truth Table

	Inputs	Outputs				
G1	G2	An	Y _n (541)	<u>Y</u> _n (540)		
Н	Х	Х	Z	Z		
Х	Н	Х	Z	Z		
L	L	Н	Н	L		
L	L	L	L	Н		

X: Don't care

Z: High impedance

Y_n: TC7MH541

 \overline{Y}_n : TC7MH540



Maximum Ratings

Characteristics	Symbol	Rating	Unit
Supply voltage range	V _{CC}	-0.5~7.0	V
DC input voltage	V _{IN}	-0.5~7.0	V
DC output voltage	V _{OUT}	-0.5~V _{CC} + 0.5	V
Input diode current	I _{IK}	-20	mA
Output diode current	lok	±20	mA
DC output current	lout	±25	mA
DC V _{CC} /ground current	Icc	±75	mA
Power dissipation	P _D	180	mW
Storage temperature	T _{stg}	-65~150	°C

Recommended Operating Conditions

Characteristics	Symbol	Rating	Unit
Supply voltage	V _{CC}	2.0~5.5	V
Input voltage	V _{IN}	0~5.5	V
Output voltage	V _{OUT}	0~V _{CC}	V
Operating temperature	T _{opr}	-40~85	°C
Input rise and fall time	dt/dv	$0\sim100 \ (V_{CC} = 3.3 \pm 0.3 \ V)$ $0\sim20 \ (V_{CC} = 5 \pm 0.5 \ V)$	ns/V



Electrical Characteristics

DC Characteristics

Characteristics		Symbol Test Condition			Ta = 25°C			Ta = -40~85°C		Unit	
		Symbol	rest Condition		V _{CC} (V)	Min	Тур.	Max	Min	Max	Unit
					2.0	1.50	_	_	1.50	_	
High level		V_{IH}	_		3.0~5.5	V _{CC} × 0.7	_	_	V _{CC} × 0.7	_	V
Input voltage					2.0	_	_	0.50	_	0.50	V
	Low level	V_{IL}	_		3.0~5.5		_	V _{CC} × 0.3	_	V _{CC} ×0.3	
	High level	V _{OH}			2.0	1.9	2.0	_	1.9	_	
			V _{IN} = V _{IH} or V _{IL}	$I_{OH} = -50 \mu A$	3.0	2.9	3.0	_	2.9	_	V
Output voltage					4.5	4.4	4.5		4.4	_	
				$I_{OH} = -4 \text{ mA}$	3.0	2.58	_	_	2.48		
				$I_{OH} = -8 \text{ mA}$	4.5	3.94	_		3.80	_	
Output Voltage	Low level	V _{OL}	V _{IN} = V _{IH} or V _{IL}		2.0	_	0	0.1		0.1	V
				$I_{OL} = 50 \mu A$	3.0	_	0	0.1	_	0.1	
					4.5	_	0	0.1	_	0.1	
				$I_{OL} = 4 \text{ mA}$	3.0	_	_	0.36	_	0.44	
				$I_{OL} = 8 \text{ mA}$	4.5	_	_	0.36	_	0.44	
3-state output off-state current		I _{OZ}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = V_{CC} \text{ or GND}$		5.5	_		±0.25	_	±2.50	μА
Input leakage cu	rrent	I _{IN}	V _{IN} = 5.5 V or GND		0~5.5		_	±0.1	_	±1.0	μΑ
Quiescent supply current I_{CC} $V_{IN} = V_{CC}$ or GND		5.5	_	_	4.0	_	40.0	μΑ			



AC Characteristics (Input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol	Test Condition			Ta = 25°C			Ta = -40~85°C		Unit
Characteristics	Syllibol	rest Condition	V _{CC} (V)	C _L (pF)	Min	Тур.	Max	Min	Max	Offic
Propagation delay time		_	3.3 ± 0.3 -	15	_	4.8	7.0	1.0	8.5	ns
	t _{pLH}			50	_	7.3	10.5	1.0	12.0	
(TC7MH540FK)	t _{pHL}		5.0 ± 0.5	15	_	3.7	5.0	1.0	6.0	
			3.0 ± 0.3	50	_	5.2	7.0	1.0	8.0	
			3.3 ± 0.3	15	_	5.0	7.0	1.0	8.5	
Propagation delay time	t _{pLH}		3.3 ± 0.3	50		7.5	10.5	1.0	12.0	ns
(TC7MH541FK)	t _{pHL}	_	5.0 ± 0.5	15		3.5	5.0	1.0	6.0	
			5.0 ± 0.5	50		5.0	7.0	1.0	8.0	
	t _{pZL} t _{pZH}	$R_L = 1 \text{ k}\Omega$	3.3 ± 0.3	15		6.8	10.5	1.0	12.5	- ns
3-state output enable time				50		9.3	14.0	1.0	16.0	
3-state output enable time			5.0 ± 0.5	15		4.7	7.2	1.0	8.5	
				50		6.2	9.2	1.0	10.5	
3-state output disable time	t _{pLZ}	$R_{I} = 1 k\Omega$	3.3 ± 0.3	50		11.2	15.4	1.0	17.5	ns
o-state output disable time	t _{pHZ}	N 1 N22	5.0 ± 0.5	50		6.0	8.8	1.0	10.0	113
Output to output skew	t _{osLH}	(Note1)	3.3 ± 0.3	50			1.5	_	1.5	ns
Output to output skew	t _{osHL}	(Note I)	5.0 ± 0.5	50		_	1.0	_	1.0	115
Input capacitance	C _{IN}	_		_	4	10	_	10	pF	
Output capacitance	C _{OUT}	_			6	_	_		pF	
Power dissipation	C _{PD}	TC7MH540FK				17	_	_	_	pF
capacitance (Note2)	CAD	TC7MH541FK		_	18	_	_	_	μ	

Note1: Parameter guaranteed by design.

 $t_{\text{OSLH}} = |t_{\text{pLHm}} - t_{\text{pLHn}}|, \, t_{\text{OSHL}} = |t_{\text{pHLm}} - t_{\text{pHLn}}|$

Note2: CPD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

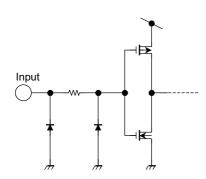
 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 \text{ (per bit)}$



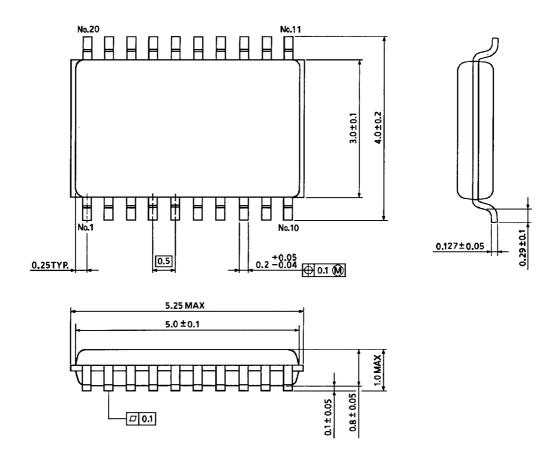
Noise Characteristics (Input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol	Test Condition		Ta = 25°C		- Unit
Gilalacteristics	Syllibol	rest Condition	V _{CC} (V)	Тур.	Limit	Offic
Quiet output maximum dynamic V _{OL}	V _{OLP}	C _L = 50 pF	5.0	0.7	1.0	V
Quiet output minimum dymnamic V _{OL}	V _{OLV}	C _L = 50 pF	5.0	-0.7	-1.0	V
Minimum high level dynamic input voltage V_{IH}	V _{IHD}	C _L = 50 pF	5.0	_	1.5	V
Maximum low level dynamic input voltage V_{IL}	V _{ILD}	C _L = 50 pF	5.0	_	3.5	V

Input Equivalent Circuit



Package Dimensions



Weight: 0.03 g (typ.)